

# 产品规格书

## SPECIFICATIONS FOR PRODUCT

产品类型	TYPE	:	HC-49SMD	
产品规格	SPEC	•	<u>32.768MHz/49SMD/20PF/20PPM</u> 矮壳	
产品型号	P/N	:	CJ03A-327682020A20	
日期	DATE	:	2022/01/18	

核准及签名			部汀
R&D APPR.	SIGNATURED		DEPT.
拟制	审核	批准	频率器件事业部
ISSUE	CHECK	APPROVAL	
Ivan	Abbey	Ken	
2022/01/18	2022/01/18	2022/01/18	

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JIANGSU CHANGJING ELECTRONICS TECHNOLOGY CO., LTD.



# HC-49/SMD Quartz Crystal

# CJ03A-327682020A20

- 1. Scope:
- 1.1 This specification applies to the RoHS/SONY compliance quartz crystal unit with a frequency of 32.768MHz which will be used in crystal oscillator applications.
- 2. Construction:
- 2.1 Type of Quartz Resonator: HC-49/SMD

#### 3. Electrical Characteristics

3.1 Nominal Frequency(f):	32.768MHz
3.2 Load Capacitance(C <sub>L</sub> ):	20pF
3.3 Frequency Tolerance( $\triangle$ f/f):	±20ppm
3.4 Frequency Temperature Stability:	<b>±20ppm(Ref.@25</b> ℃)
3.5 Resonance Resistance(ohm):	30ohms Max
3.6 Osc mode:	Fundamental mode
3.7 Shunt Capacitance(C <sub>0</sub> ):	<7pF
3.8 Drive Level(D <sub>L</sub> ):	<300µW
3.9 Operating Temperature Range(T <sub>OPR</sub> ):	-20 to + 70°C
3.10 Storage Temperature Range(T <sub>STG</sub> ):	-55 to + 125°C
3.11 Insulation Resistance(IR):	>500 M ohms
3.12 Aging(△f <sub>A</sub> ):	± 3ppm per Year

## 4. Reliability Specifications

This is the quality control and quality assurance and reliability tests performance data for the RoHS/

SONYcompliance 32.768MHz HC-49/SMD Quartz Crystal.

related to the specification and approval sheet provided by JSCJ.

Standard test condition (TEMP.: 20±5°C. Relative humidity: 65±20%)

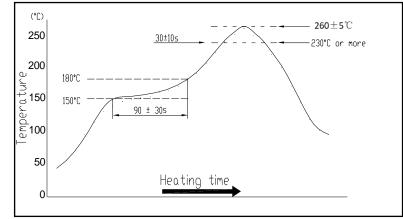
For any discrepancy in GO/NG, test will be done at TEMP.25±2°C, R.H. 65±5%.

NO.	PROCESS	SPECIFICATION	TEST METHOD
4.1	Temperature Cycle (GB/T 2423.22-2002, Method Nb)	Frequency change after test ≤± 5ppm.Resonance resistance change after test ≤10ohms.	10 cycles from -55°C to 125°C. Measurement taken after DUT being left at room temperature for 24±2 hours.
4.2	Low Temperature Storage (GB/T 2423.1-2001, Method Aa)	Frequency change after test ≤± 5ppm.Resonance resistance change after test ≤10ohms.	Spending 72 hrs at -55°C±3°C constant temperature. Measurement taken after DUT being left at room temperature for 24±2 hours.
4.3	High Temperature Storage (GB/T 2423.2-2001, Method Ba)	Frequency change after test ≤± 5ppm.Resonance resistance change after test ≤10ohms.	Spending 72 hrs at 125°C±3°C constant temperature. Measurement taken after DUT being left at room temperature for 24±2 hours.
4.4	Humidity (GB/T 2423.3- 2006, Method Cab)	Frequency change after test ≤± 5ppm.Resonance resistance change after test ≤10ohms.	Spending 96 hrs at 40 °C $\pm$ 3 °C, with 93 %R.H, Then keep the DUT in dry oven at 40 $\pm$ 5 °C for 24 hour. Measurement taken after DUT being left at room temperature for 1 to 2 hours.
4.5	Vibration (GB/T 2423.10- 1995, Method Fc)	Frequency change after test ≤± 5ppm.Resonance resistance change after test ≤10ohms.	Apply 0.75mm vibration at sweep frequency $10^{\sim}$ 500 Hz, 10 cycles in each direction of 3 axis. Measurement taken after 1 hour.
4.6	Shock (GB/T 2423.5-1995, Method Ea)	Frequency change after test $\leq \pm$ 5ppm.Resonance resistance change after test $\leq$ 10ohms.and exhibit no visible damage.	Peak 1000m/s2, normal width 6ms half sine wave form, 3.7m/s, 3 perpendicular axis of samples, 3 cycles / direction, total 18 cycles. Measurement taken after 1 hour.
4.7	Drop (GB/T 2423.8-1995, Method Ed)	Frequency change after test $\leq \pm$ 5ppm.Resonance resistance change after test $\leq$ 10ohms.and exhibit no visible damage.	Free drop to the steel plate with thickness of 3 mm from 0.75 m heights for 3 times.
4.8	Solderability (IEC60068-2- 58,Test Td:)	Terminals shall be covered more then 95% with solder.	Passed through the re-flow oven under the following condition. Preheat 150 to $180^{\circ}$ C for 60 to 120sec, and soldering time for $20s \pm 5s$ at $235^{\circ}$ C, peak soldering time for $10s \pm 1s$ betweein 240 and 250°C. There is no need to do functional test. 8-12X magnifier.
4.9	Terminal Strength (JIS-C- 6429 Method 1 & 2 )	No visible damage	Mount on a glass-epoxy board (100x50x1.6mm), then bend to 2mm displacement (velocity 1mm/sec) and keep for 5 seconds. or pulling force 0.5kg for at least 60 seconds.
4.10	Resistance to Soldering Heat (IEC60068-2-58,Test Td: Table 4)	Frequency change after test ≤± 5ppm.Resonance resistance change after test ≤10ohms.	Passed through the re-flow oven under the following condition. Preheat 150 to 180°C for 60 to 120sec, and sodering time for 60s max at 235°C, peak soldering time for 20s max at 265°C max. Measurement taken after DUT being left at room temperature for at least 2 hours.
4.11	OTHERS		

5. Recommended Reflow soldering condition (SMD)

Solder profile

Peak: 260±5°C Soldering zone: 230°C or more, 30±10s. Pre-heating zone 1: 150 $\sim$  180°C, 90±30s



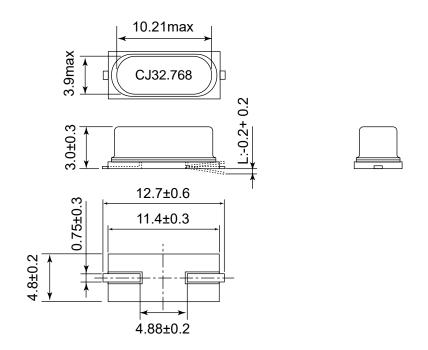
Temperature profile for reflow soldering

### 6. Soldering iron method

Bit temperature:  $350\pm10^{\circ}$ C Application time of soldering iron:3+1 s. For other procedures, refer to IEC 60068-2-20.

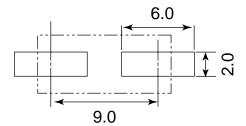
#### **Package Outline Dimensions**

#### Units:mm



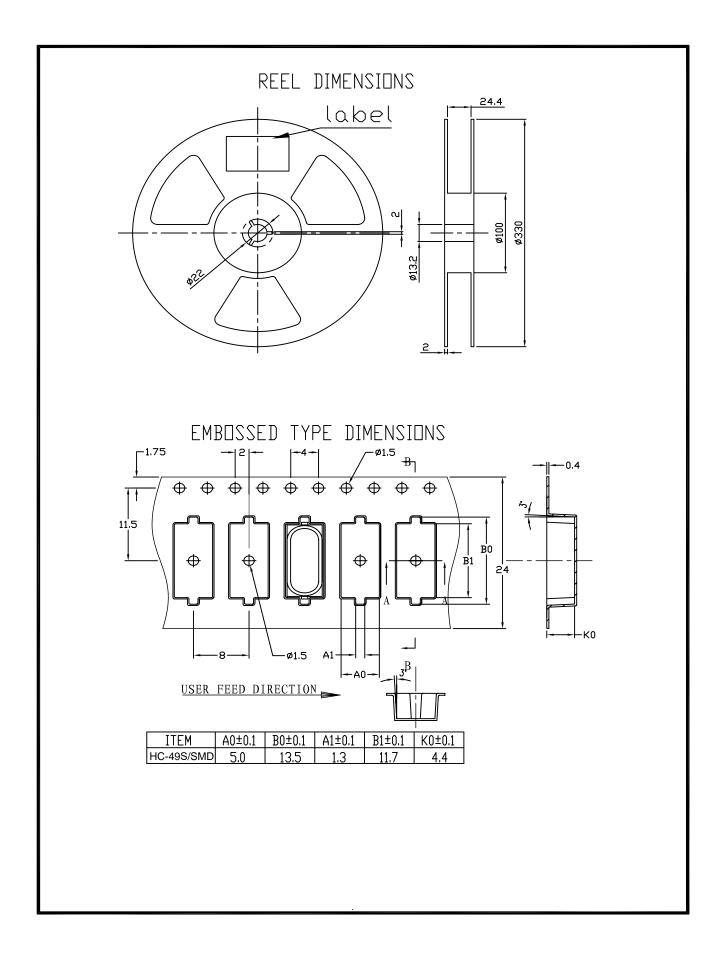
### Suggested Pad Layout

Units:mm



#### NOTICE

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